Not Recommended for New Design Use DMG4406LSS





N-CHANNEL ENHANCEMENT MODE MOSFET

DMG8880LSS

Features

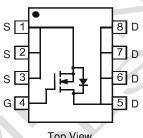
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)



Top View



Top View Internal Schematic

Ordering Information (Note 4)

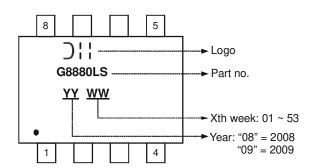
Part Number	Case	Packaging
DMG8880LSS-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information







Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T _A = 25°C T _A = 70°C	ID	11.6 8.5	А
Pulsed Drain Current (Note 6)			I _{DM}	80	Α

Thermal Characteristics

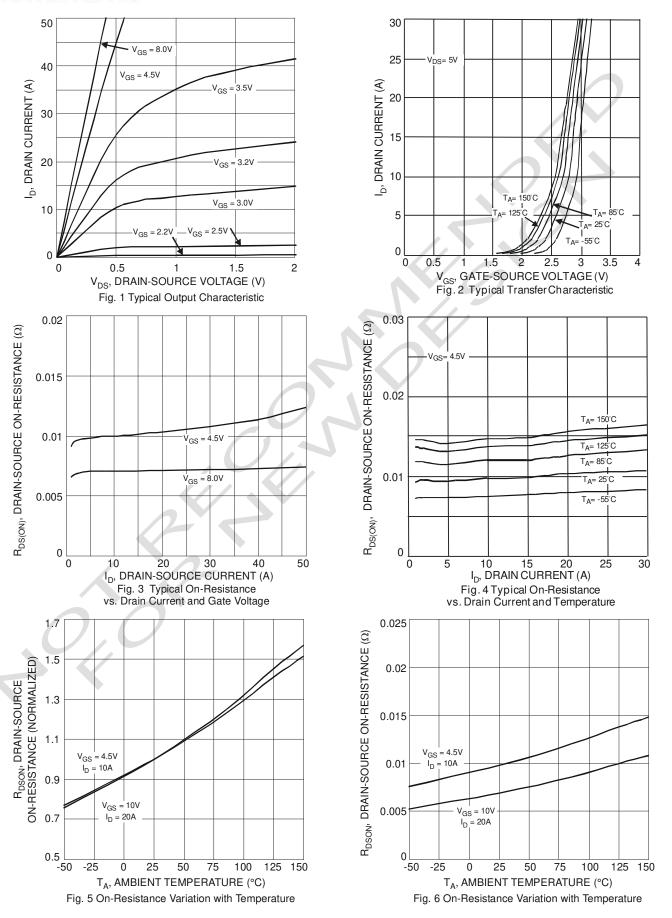
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.43	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5)	R _• JA	87	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.0	٧	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		7.0	10 14	m•	$V_{GS} = 10V, I_D = 11.6A$	
Static Drant-Source Off-Nesistance	R _{DS (ON)}	-	9.6			$V_{GS} = 4.5V, I_D = 10.7A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C _{iss}	-	1289	-	рF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	187	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	162	-	pF		
Gate Resistance	R_{g}	-	0.97	-	•	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at 10V	Qg	-	27.6	-	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 11.6A, I _G = 1.0mA	
Total Gate Charge at 5V	Q_g	-	14.4	-	nC	V 5V V 15V	
Gate-Source Charge	Q_{gs}	-	3.6	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$ $I_{D} = 11.6A, I_{G} = 1.0mA$	
Gate-Drain Charge	Q_{gd}	-	4.9	-	nC	ID = 11.6A, IG = 1.0IIIA	
Turn-On Delay Time	$t_{D(on)}$	-	7.04	-	ns		
Turn-On Rise Time	tr	-	17.52	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	-	36.13	-	ns	R _{GS} = 11• , I _D = 11.6A	
Turn-Off Fall Time	t _f	-	19.67	-	ns		

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
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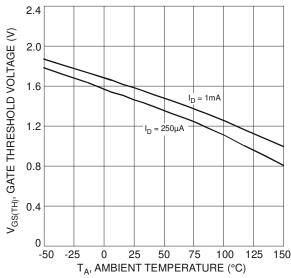
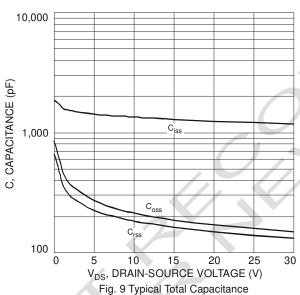
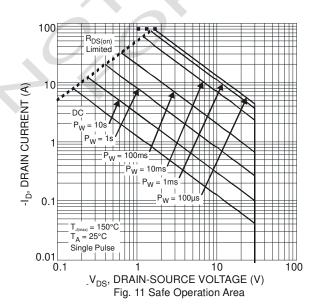
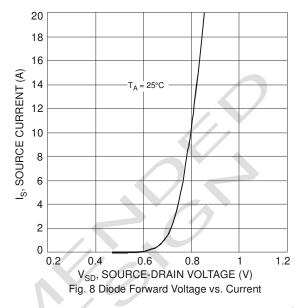
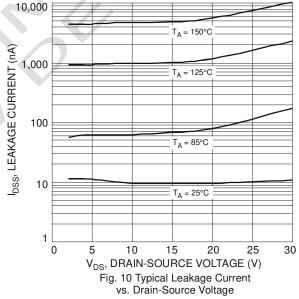


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

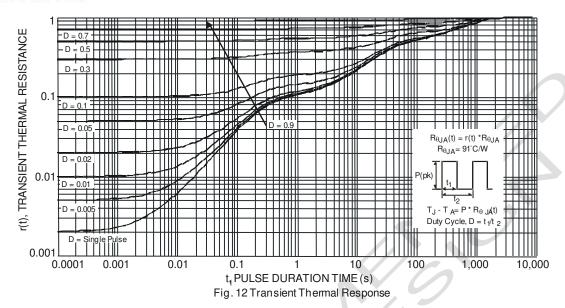




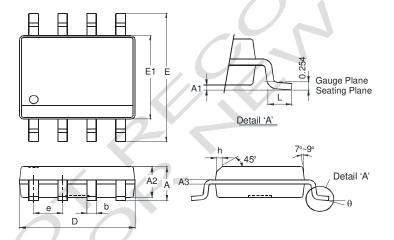






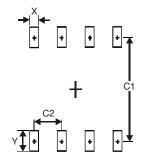


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	1	1.75			
A 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
q	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	•	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27

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